UNITED STATES PATENT AND TRADEMARK OFFICE CERTIFICATE OF CORRECTION

PATENT NO. : 6,800,876 B2

DATED : October 5, 2004 INVENTOR(S) : Edmond et al.

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Title page,

Item [54] Title, reads "GROUP III NITRIDE LED WITH UNDOPED CLADDING LAYER (5000.137)" should read -- GROUP III NITRIDE LED WITH UNDOPED CLADDING LAYER AND MULTIPLE QUANTUM WELL --.

Item [75], Inventors, "Hua-shuang Kong" should read -- Hua-Shuang Kong -- Item [56], References Cited, U.S. PATENT DOCUMENTS, reads "5,670,798 A 9/1997 Kimura" should read -- 5,670,798 A 9/1997 Schetzina -- CTHER PUBLICATIONS "For all Public ATIONS "Fo

OTHER PUBLICATIONS, "Expert Report P-N Junction Location and Layer Conductivity in InGaN LED Chips Manufactured By"." should read

- -- "Expert Report P-N Junction Location and Layer Conductivity in InGaN LED Chips Manufactured By Cree, Inc." --.
- ""Expert Report Title: Structure and Analysis of InGaN LED Chips Manufactured By"." should read
- -- "Expert Report Title: Structure and Analysis of InGaN LED Chips Manufactured by Cree Inc." --.

Column 15,

Line 12, "Group III" should read -- Group III --.
Line 22, "where 0.ltoreq.x<1 and 0.ltoreq.y.ltoreq.1" should read

-- where 0.ltoreq.xltoreq.1 and 0ltoreq.y.<1 --.

Signed and Sealed this

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Second Day of August, 2005

JON W. DUDAS
Director of the United States Patent and Trademark Office